

RoHS

N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(m\Omega)(Typ.)$	I _D (A) ^a	Q _g (Typ.)			
40	2.2 at V _{GS} = 10 V	104	110 nC			
40	3 at V _{GS} = 4.5 V	104				

Din-Tek SEMICONDUCTOR

FEATURES

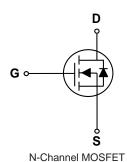
- DT-Trench Power MOSFET
- 100 % Rg and UIS tested
- · High Power and Current Handing Capability
- · Lead Free Product is Acquired

APPLICATIONS

- POL Applications
- Ideal for High-Frequency Switching and Synchronous Ectification

DFN5X6-8L Pin Configuration





ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V _{DS}	40	V			
Gate-Source Voltage	V _{GS}	± 20				
Operation of Paris Courses (T. 450.00)2	T _C = 25 °C	,	104	А		
Continuous Drain Current (T _J = 150 °C) ^a	T _C = 100 °C	I _D	66			
Pulsed Drain Current ^b	I _{DM}	416				
Single Avalanche Energy	E _{AS}	441	mJ			
Maximum Power Dissipation ^c	T _C = 25 °C	В	92	W		
waximum rower bissipation	T _C = 100 °C	P _D	37] vv		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^d	R _{thJA}	55	°C/W		
Junction-to-Case (Drain)	R _{thJC}	1.3			

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{8JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	40	-	-	V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1	-	2.5	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	μΑ	
Zero Gate Voltage Drain Current	l	$V_{DS} = 40 V, V_{GS} = 0 V$	-	-	1	μΑ	
Zelo Gate Voltage Diam Current	I _{DSS}	$V_{DS} = 32 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 \text{ °C}$	-	-	100		
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ 5 V, V _{GS} = 10 V	104	-	-	Α	
Drain-Source On-State Resistance ^a	D	V _{GS} = 10 V, I _D = 20 A	-	2.2	2.9		
Dialii-Source On-State Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 20 A	-	3	4	mΩ	
Forward Transconductancea	9 _{fs}	$V_{DS} = 5 \text{ V}, I_{D} = 20 \text{ A}$	-	68	-	S	
Dynamic ^b							
Input Capacitance	C _{iss}		-	6130	-	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$	-	401	-		
Reverse Transfer Capacitance	C _{rss}		-	348	-		
Total Gate Charge ^c	Q_g		-	110	-	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	20	-		
Gate-Drain Charge ^c	Q_{gd}		-	20	-		
Gate Resistance			-	1	-	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	14	-		
Rise Time ^c	t _r	V_{DD} = 20 V, R_L = 1 Ω , R_{GEN} = 6 Ω	-	26	-		
Turn-Off Delay Time ^c	t _{d(off)}	V _{GS} = 10 V	-	77	-	ns	
Fall Time ^c	t _f		-	22	-		
Drain-Source Body Diode Ratings and	Characterist	ics ^b (T _J = 25 °C)					
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	104	Α	
Pulsed Current	I _{SM}		-	-	416	Α	
Forward Voltage ^a	V _{SD}	I _F = 20 A, V _{GS} = 0 V	-	-	1.2	V	
Reverse Recovery Time	t _{rr}	1 00 4 4744 400 475	-	25	-	ns	
Reverse Recovery Charge	Q_{rr}	$I_F = 20 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$	-	16	-	nC	

Notes

- a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended pe riods may affect device reliability.



TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)

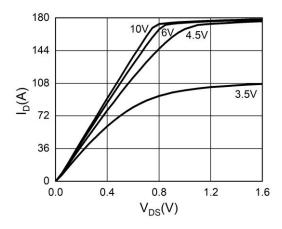


Fig.1 Typical Output Characteristics

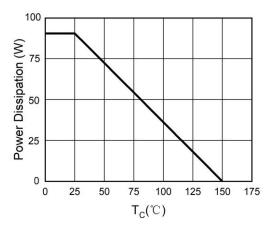


Fig. 3 Power Dissipation

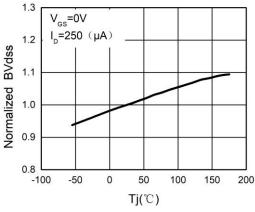


Fig. 5 BVDSS vs Junction Temperature

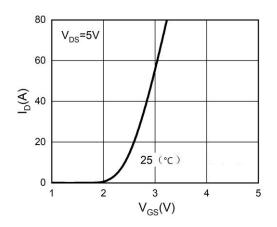


Fig.2 Transfer Characteristics

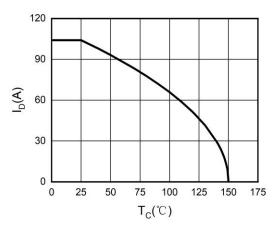


Fig. 4 Drain Current

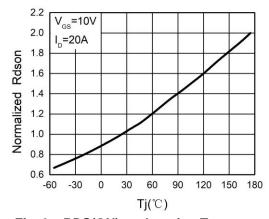


Fig. 6 RDS(ON) vs Junction Temperature



TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)

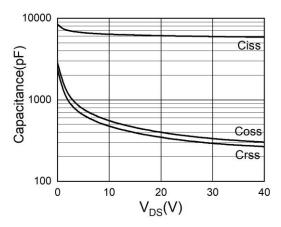


Fig. 7 Capacitance

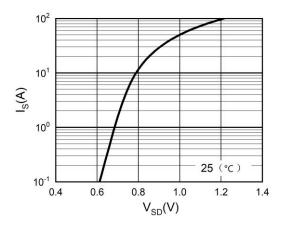
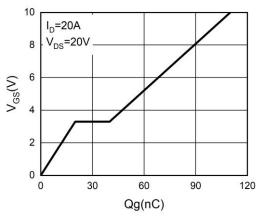
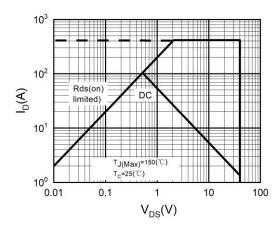


Fig. 9 Body-Diode Characteristics



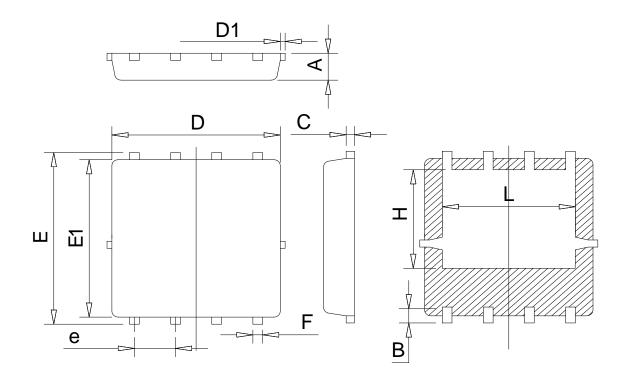
Gate Charge Waveforms



Maximum Safe Operation Area Fig. 10



DFN5X6-8L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max
А	0.78	0.95	1.12
В	0.45	0.58	0.78
С	0.18	0.254	0.36
D	4.70	5.20	5.45
D1			0.18
Е	5.85	6.05	6.25
E1	5.38	5.55	5.98
е	1.15	1.27	1.40
F	0.18	0.30	0.52
Н	3.25	3.47	3.70
L	3.75	4.00	4.25





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